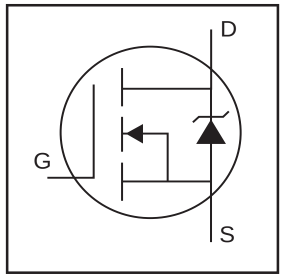
PD - 91337

International
IOR Rectifier

IRL3103

HEXFET® Power MOSFET

- Advanced Process Technology
- Ultra Low On-Resistance
- Dynamic dv/dt Rating
- 175°C Operating Temperature
- Fast Switching
- Fully Avalanche Rated



V_{DSS} = 30V

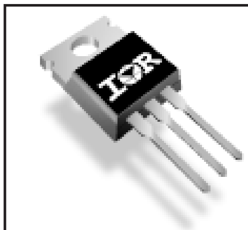
$R_{DS(on)}$ = 12mΩ

I_D = 64A

Description

Advanced HEXFET® Power MOSFETs from International Rectifier utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in a wide variety of applications.

The TO-220 package is universally preferred for all commercial-industrial applications at power dissipation levels to approximately 50 watts. The low thermal resistance and low package cost of the TO-220 contribute to its wide acceptance throughout the industry.



TO-220AB

Absolute Maximum Ratings

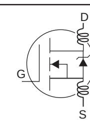
	Parameter	Max.	Units
I_D @ T_C = 25°C	Continuous Drain Current, V_{GS} @ 10V	64	A
I_D @ T_C = 100°C	Continuous Drain Current, V_{GS} @ 10V	45	
I_{DM}	Pulsed Drain Current ①	220	
P_D @T_C = 25°C	Power Dissipation	94	W
	Linear Derating Factor	0.63	W/°C
V_{GS}	Gate-to-Source Voltage	± 16	V
I_{AR}	Avalanche Current①	34	A
E_{AR}	Repetitive Avalanche Energy①	22	mJ
dv/dt	Peak Diode Recovery dv/dt ③	5.0	V/ns
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to + 175	°C
	Soldering Temperature, for 10 seconds	300 (1.6mm from case)	
	Mounting torque, 6-32 or M3 srew	10 lbf•in (1.1N•m)	

Thermal Resistance

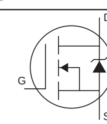
	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	——	1.6	°C/W
$R_{\theta CS}$	Case-to-Sink, Flat, Greased Surface	0.50	——	
$R_{\theta JA}$	Junction-to-Ambient	——	62	

3/16/01

Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	30	——	——	V	V_{GS} = 0V, I_D = 250µA
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	——	0.028	——	V/°C	Reference to 25°C, I_D = 1mA
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	——	——	12	mΩ	V_{GS} = 10V, I_D = 34A ④
		——	——	16		V_{GS} = 4.5V, I_D = 28A ④
$V_{GS(th)}$	Gate Threshold Voltage	1.0	——	——	V	V_{DS} = V_{GS}, I_D = 250µA
g_{fs}	Forward Transconductance	22	——	——	S	V_{DS} = 25V, I_D = 34A④
I_{DSS}	Drain-to-Source Leakage Current	——	——	25	µA	V_{DS} = 30V, V_{GS} = 0V
		——	——	250		V_{DS} = 24V, V_{GS} = 0V, T_J = 150°C
I_{GSS}	Gate-to-Source Forward Leakage	——	——	100	nA	V_{GS} = 16V
	Gate-to-Source Reverse Leakage	——	——	-100		V_{GS} = -16V
Q_g	Total Gate Charge	——	——	33	nC	I_D = 34A
Q_{gs}	Gate-to-Source Charge	——	——	5.9		V_{DS} = 24V
Q_{gd}	Gate-to-Drain ("Miller") Charge	——	——	17		V_{GS} = 4.5V, See Fig. 6 and 13
$t_{d(on)}$	Turn-On Delay Time	——	8.9	——		V_{DD} = 15V
t_r	Rise Time	——	120	——		I_D = 34A
$t_{d(off)}$	Turn-Off Delay Time	——	14	——		R_G = 1.8Ω
t_f	Fall Time	——	9.1	——		V_{GS} = 4.5V, See Fig. 10 ④
L_D	Internal Drain Inductance	——	4.5	——	nH	Between lead, 6mm (0.25in.) from package and center of die contact 
L_S	Internal Source Inductance	——	7.5	——		
C_{iss}	Input Capacitance	——	1650	——	pF	V_{GS} = 0V
C_{oss}	Output Capacitance	——	650	——		V_{DS} = 25V
C_{rss}	Reverse Transfer Capacitance	——	110	——		ƒ = 1.0MHz, See Fig. 5
E_{AS}	Single Pulse Avalanche Energy②	——	1320⑤	130⑥	mJ	I_{AS} = 34A, L = 0.22mH

Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	——	——	64	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I_{SM}	Pulsed Source Current (Body Diode)①	——	——	220		
V_{SD}	Diode Forward Voltage	——	——	1.2	V	T_J = 25°C, I_S = 34A, V_{GS} = 0V ④
t_{rr}	Reverse Recovery Time	——	57	86	ns	T_J = 25°C, I_F = 34A
Q_{rr}	Reverse Recovery Charge	——	110	170	nC	di/dt = 100A/µs ④
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L_S+L_D)				

Notes:

① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)

② Starting T_J = 25°C, L = 220µH R_G = 25Ω, I_{AS} = 34A, V_{GS}=10V (See Figure 12)

③ I_{SD} ≤ 34A, di/dt ≤ 120A/µs, V_{DD} ≤ $V_{(BR)DSS}$, T_J ≤ 175°C

④ Pulse width ≤ 400µs; duty cycle ≤ 2%.

⑤ This is a typical value at device destruction and represents operation outside rated limits.

⑥ This is a calculated value limited to T_J = 175°C .

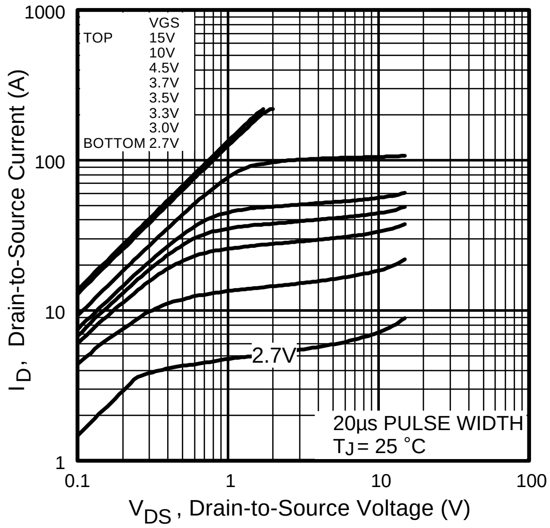


Fig 1. Typical Output Characteristics

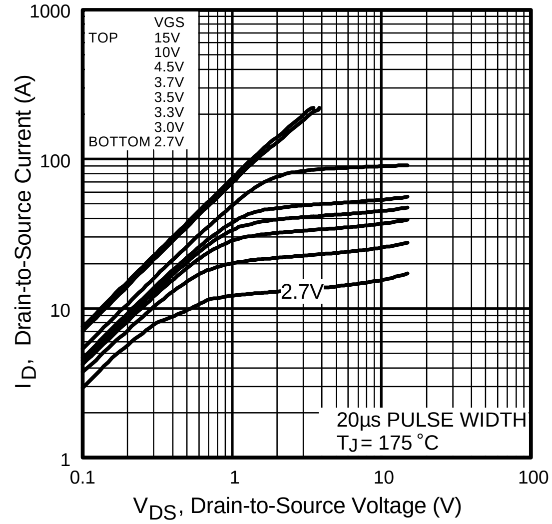


Fig 2. Typical Output Characteristics

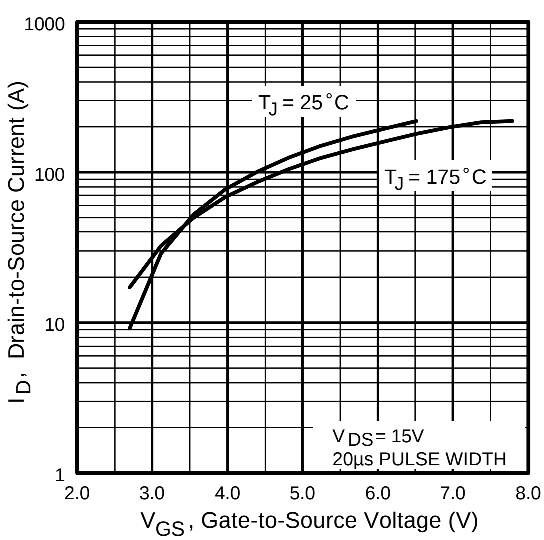


Fig 3. Typical Transfer Characteristics

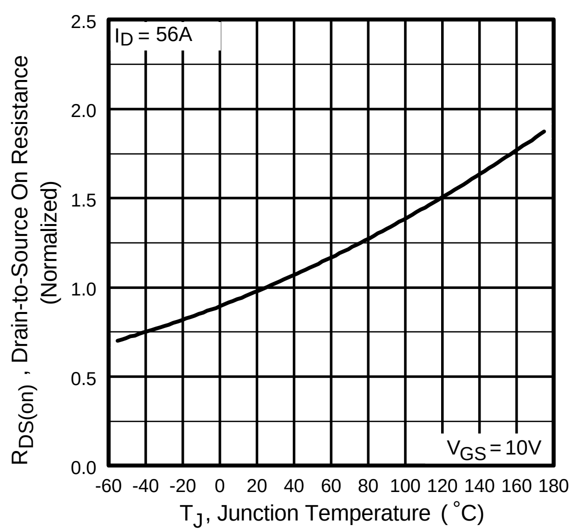


Fig 4. Normalized On-Resistance
Vs. Temperature

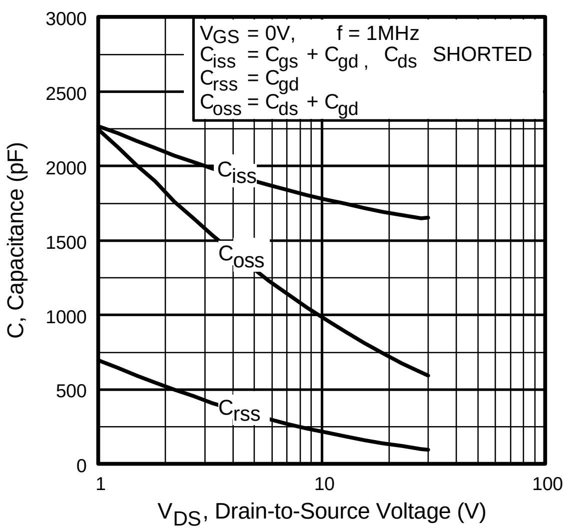


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

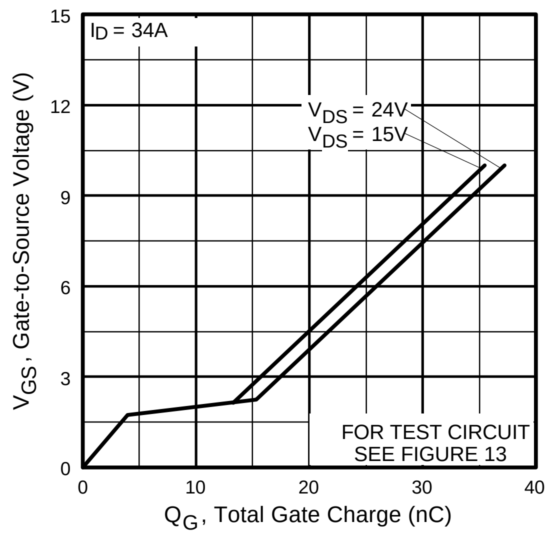


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

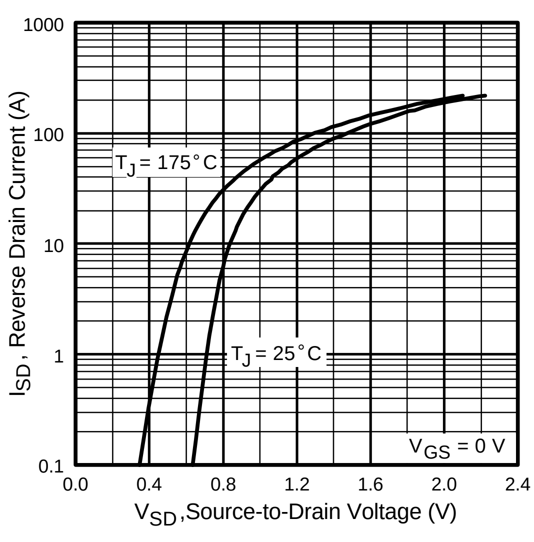


Fig 7. Typical Source-Drain Diode Forward Voltage

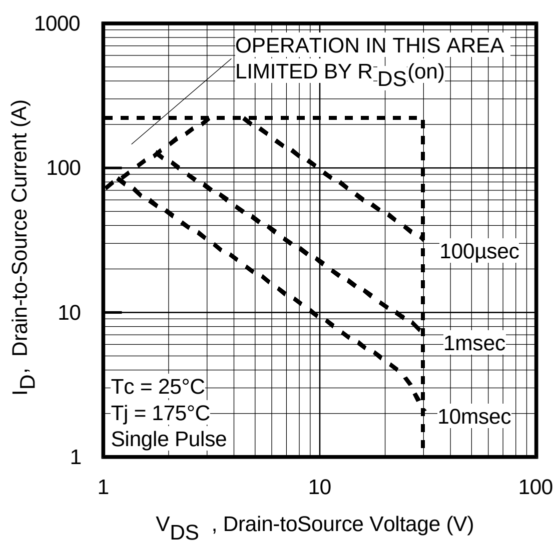


Fig 8. Maximum Safe Operating Area

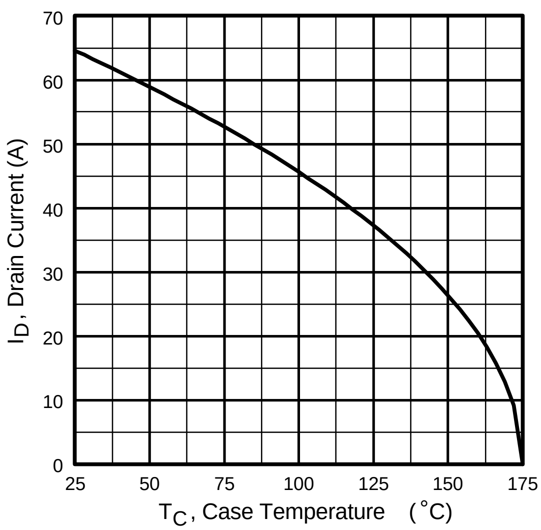


Fig 9. Maximum Drain Current Vs. Case Temperature

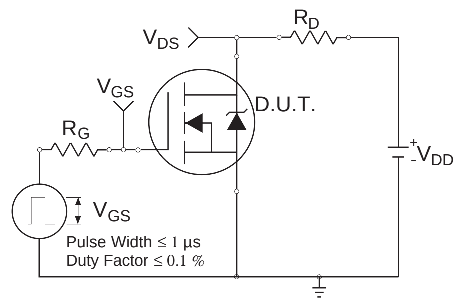


Fig 10a. Switching Time Test Circuit

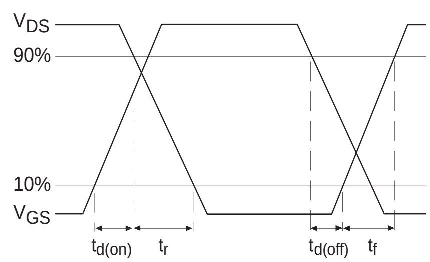


Fig 10b. Switching Time Waveforms

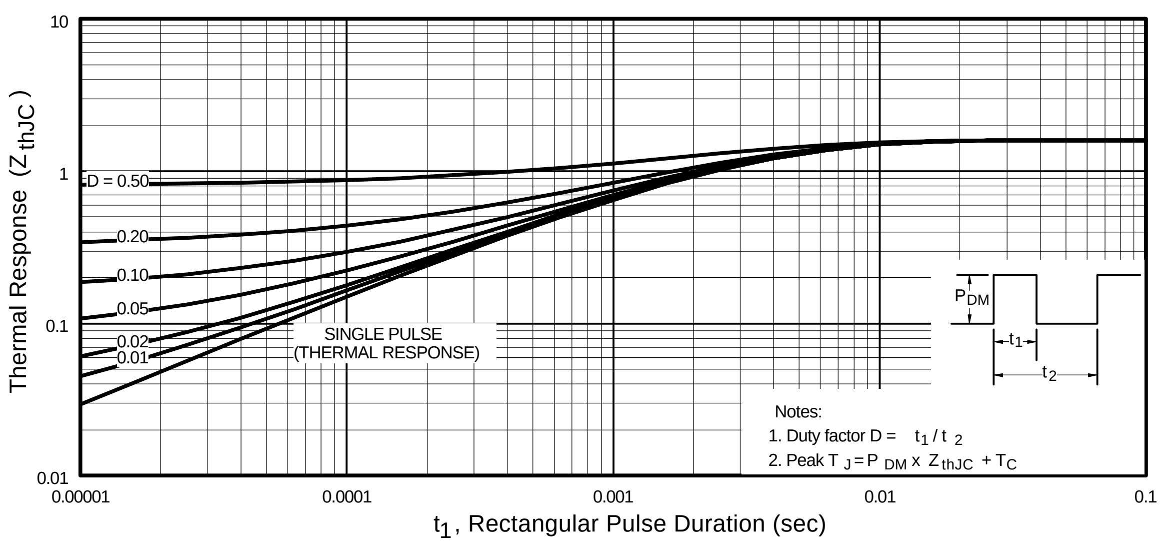


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

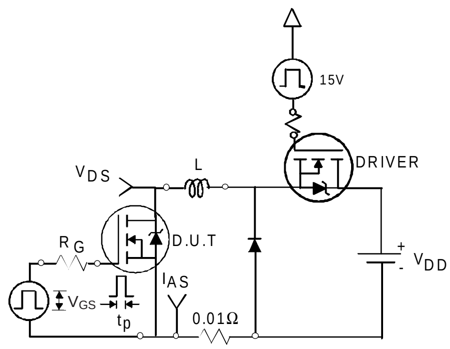


Fig 12a. Unclamped Inductive Test Circuit

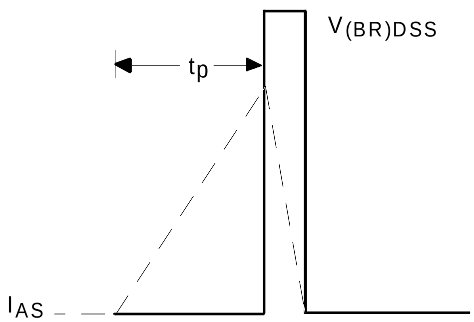


Fig 12b. Unclamped Inductive Waveforms

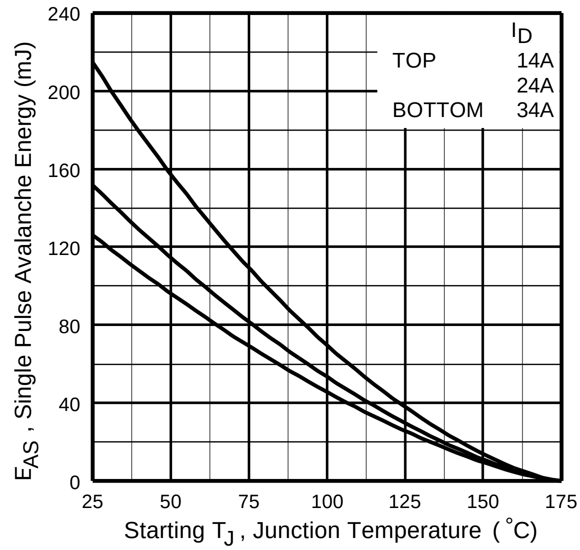


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

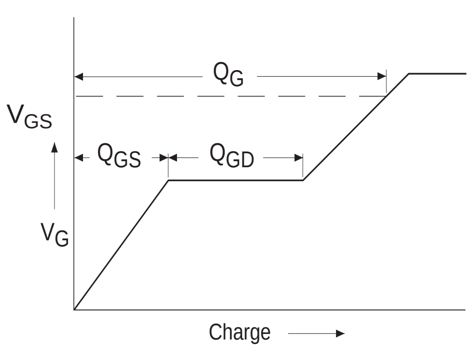


Fig 13a. Basic Gate Charge Waveform

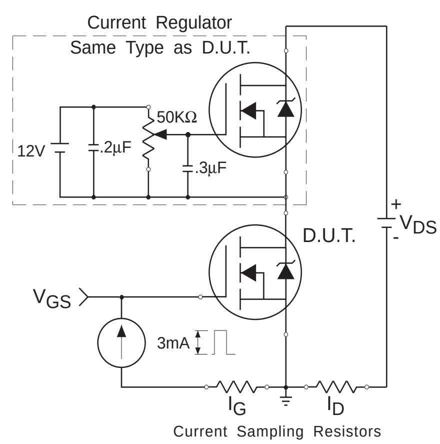
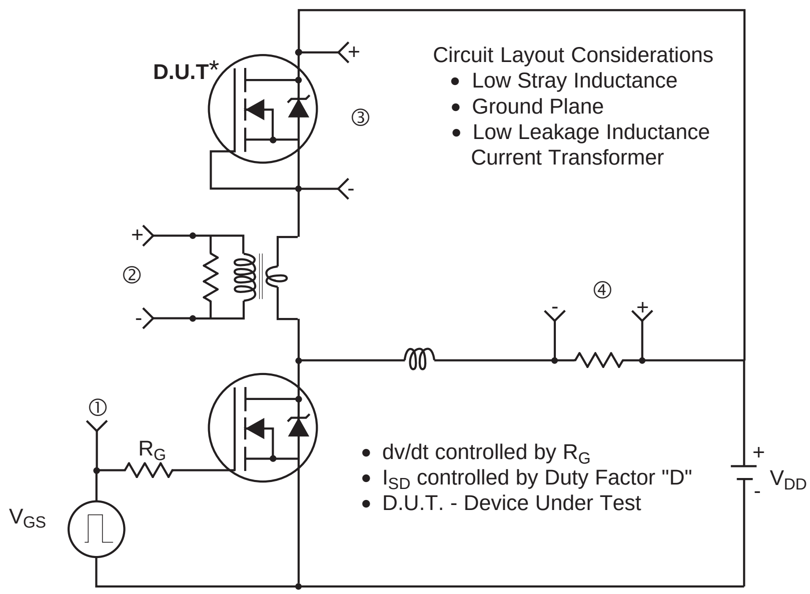
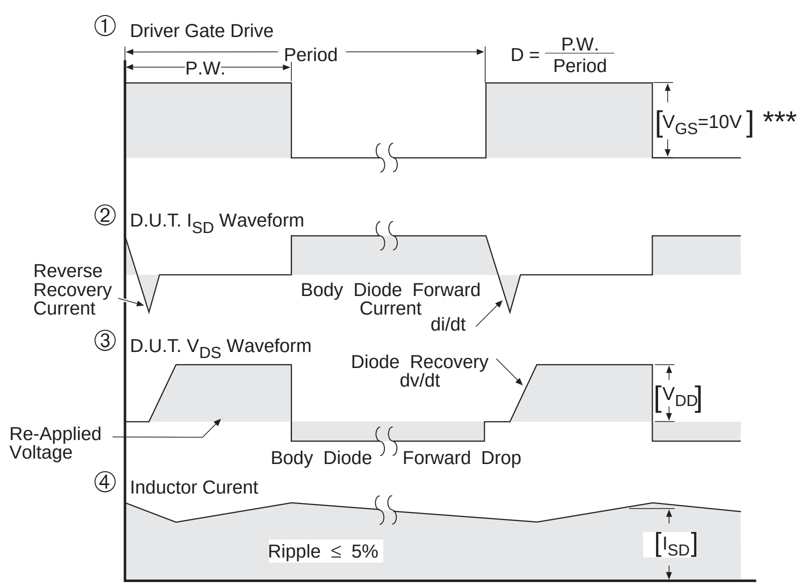


Fig 13b. Gate Charge Test Circuit

Peak Diode Recovery dv/dt Test Circuit



* Reverse Polarity of D.U.T for P-Channel



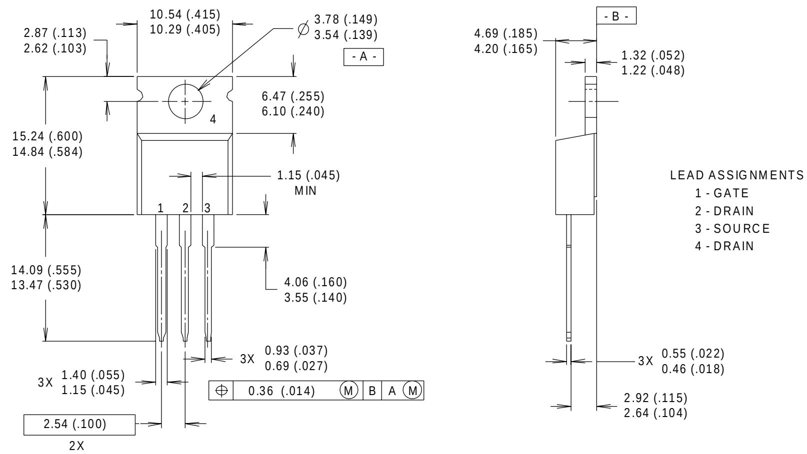
*** V_{GS} = 5.0V for Logic Level and 3V Drive Devices

Fig 14. For N-channel HEXFET® power MOSFETs

Package Outline

TO-220AB

Dimensions are shown in millimeters (inches)



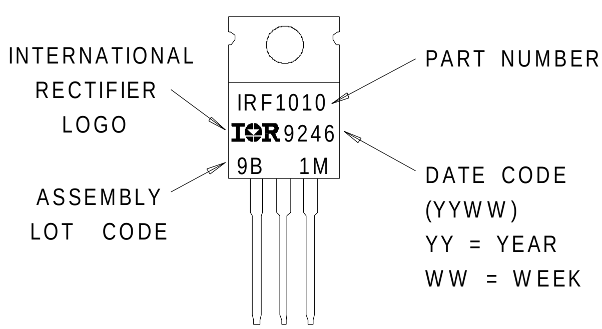
NOTES:

1 DIMENSIONING & TOLERANCING PER ANSI Y14.5M, 1982.
2 CONTROLLING DIMENSION : INCH
3 OUTLINE CONFORMS TO JEDEC OUTLINE TO-220AB.
4 HEATSINK & LEAD MEASUREMENTS DO NOT INCLUDE BURRS.

Part Marking Information

TO-220AB

EXAMPLE : THIS IS AN IRF1010
WITH ASSEMBLY
LOT CODE 9B1M



Data and specifications subject to change without notice.
This product has been designed and qualified for the industrial market.
Qualification Standards can be found on IR's Web site.

International
IOR Rectifier

IR WORLD HEADQUARTERS: 233 Kansas St., El Segundo, California 90245, USA Tel: (310) 252-7105
TAC Fax: (310) 252-7903
Visit us at www.irf.com for sales contact information. 3/01

Note: For the most current drawings please refer to the IR website at:
http://www.irf.com/package/